ABSTRACT OF THE DISCLOSURE

First characteristic values (SS, FF) which fluctuate most of the characteristic of a device composing a semiconductor device are obtained according to a fluctuation of manufacturing process for the semiconductor device. Next, the width (optimized K value) of a fluctuation width of manufacturing process which matches second characteristic values (C1, C16) of the worst cases of the characteristic of this device with the first characteristic values (SS, FF) is determined. Finally, a third characteristic value of the worst case of the circuit characteristic of the semiconductor device is determined based on this fluctuation width (optimized K value).